Transistor

2.5V Drive Nch MOS FET

2SK3019

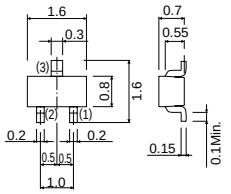
●**Structure**
Silicon N-channel
MOSFET

●**Applications**
Interfacing, switching (30V, 100mA)

●**Features**
1) Low on-resistance.
2) Fast switching speed.
3) Low voltage drive (2.5V) makes this device ideal for portable equipment.
4) Drive circuits can be simple.
5) Parallel use is easy.

●**Dimensions** (Unit : mm)

EMT3



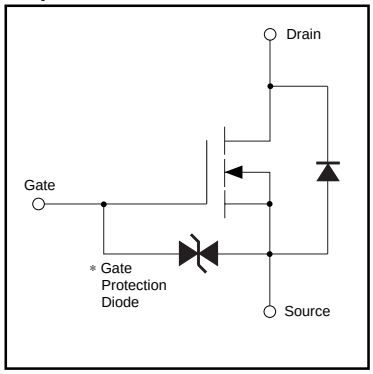
(1)Source
(2)Gate
(3)Drain

Abbreviated symbol : KN

●**Packaging specifications**

Type	Package	Taping
	Code	TL
	Basic ordering unit (pieces)	3000
2SK3019		◯

●**Equivalent circuit**



∗A protection diode is included between the gate and the source terminals to protect the diode against static electricity when the product is in use. Use a protection circuit when the fixed voltages are exceeded.

●**Absolute maximum ratings** (Ta=25°C)

Parameter		Symbol	Limits	Unit
Drain-source voltage		V_{DSS}	30	V
Gate-source voltage		V_{GSS}	±20	V
Drain current	Continuous	I_D	±100	mA
	Pulsed	I_{DP}∗1	±400	mA
Total power dissipation		P_D∗2	150	mW
Channel temperature		Tch	150	°C
Storage temperature		Tstg	−55 to +150	°C

∗1 Pw≤10μs, Duty cycle≤1%
∗2 With each pin mounted on the recommended lands.

●**Thermal resistance**

Parameter	Symbol	Limits	Unit
Channel to ambient	Rth(ch-a) ∗	833	°C / W

∗ With each pin mounted on the recommended lands.

●**Electrical characteristics** (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Gate-source leakage	I_{GSS}	–	–	±1	μA	V_{GS}=±20V, V_{DS}=0V
Drain-source breakdown voltage	$V_{(BR)DSS}$	30	–	–	V	I_D=10μA, V_{GS}=0V
Zero gate voltage drain current	I_{DSS}	–	–	1.0	μA	V_{DS}=30V, V_{GS}=0V
Gate threshold voltage	$V_{GS(th)}$	0.8	–	1.5	V	V_{DS}=3V, I_D=100μA
Static drain-source on-state resistance	$R_{DS(on)}$	–	5	8	Ω	I_D=10mA, V_{GS}=4V
	$R_{DS(on)}$	–	7	13	Ω	I_D=1mA, V_{GS}=2.5V
Forward transfer admittance	$\|Y_{fs}\|$	20	–	–	ms	I_D=10mA, V_{DS}=3V
Input capacitance	C_{iss}	–	13	–	pF	V_{DS}=5V
Output capacitance	C_{oss}	–	9	–	pF	V_{GS}=0V
Reverse transfer capacitance	C_{rss}	–	4	–	pF	f=1MHz
Turn-on delay time	$t_{d(on)}$	–	15	–	ns	I_D=10mA, V_{DD} ≒5V
Rise time	t_r	–	35	–	ns	V_{GS}=5V
Turn-off delay time	$t_{d(off)}$	–	80	–	ns	R_L=500Ω
Fall time	t_f	–	80	–	ns	R_G=10Ω

●**Electrical characteristic curves**

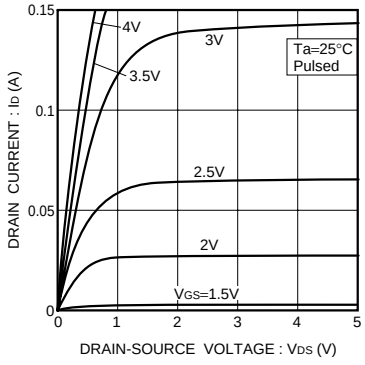


Fig.1 Typical output characteristics

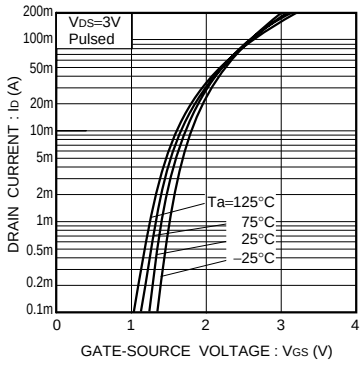


Fig.2 Typical transfer characteristics

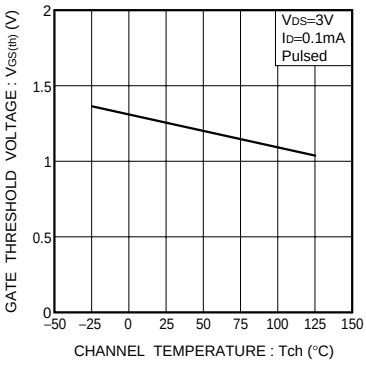


Fig.3 Gate threshold voltage vs. channel temperature

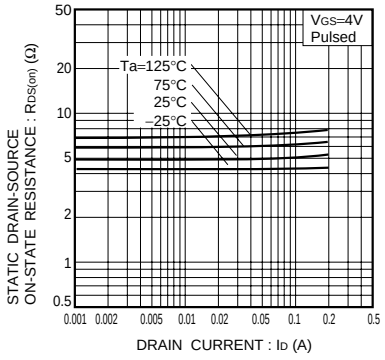


Fig.4 Static drain-source on-state resistance vs. drain current (I)

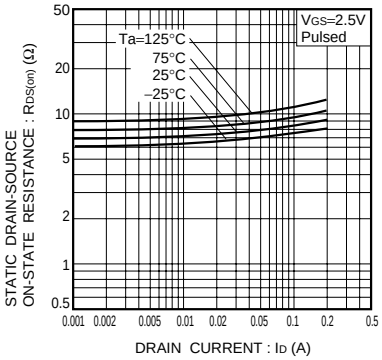


Fig.5 Static drain-source on-state resistance vs. drain current (II)

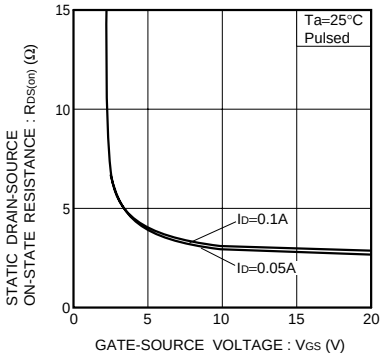


Fig.6 Static drain-source on-state resistance vs. gate-source voltage

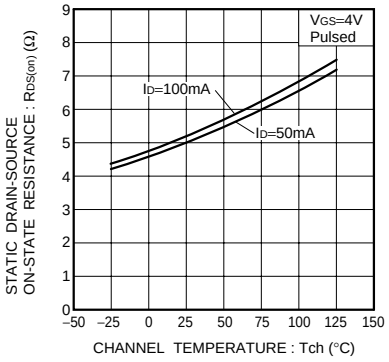


Fig.7 Static drain-source on-state resistance vs. channel temperature

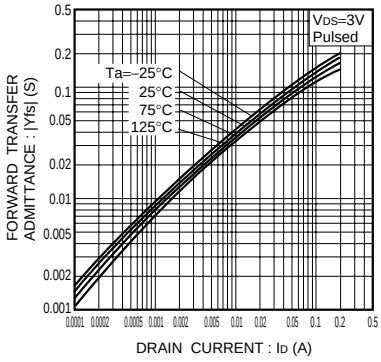


Fig.8 Forward transfer admittance vs. drain current

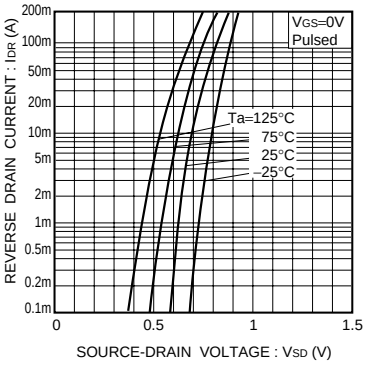


Fig.9 Reverse drain current vs. source-drain voltage (I)

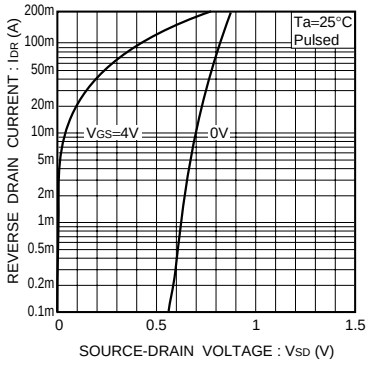


Fig.10 Reverse drain current vs. source-drain voltage (II)

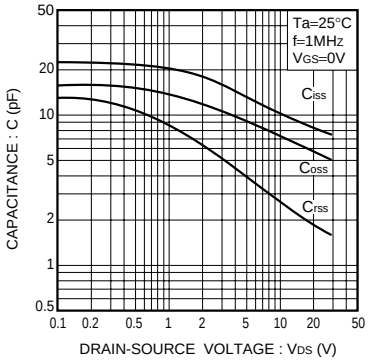


Fig.11 Typical capacitance vs. drain-source voltage

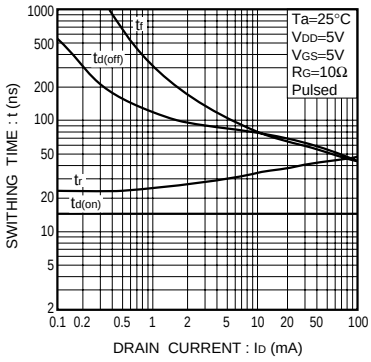


Fig.12 Switching characteristics (See Figures 13 and 14 for the measurement circuit and resultant waveforms)

●Switching characteristics measurement circuit

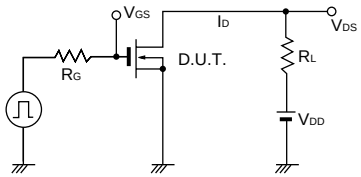


Fig.13 Switching time measurement circuit

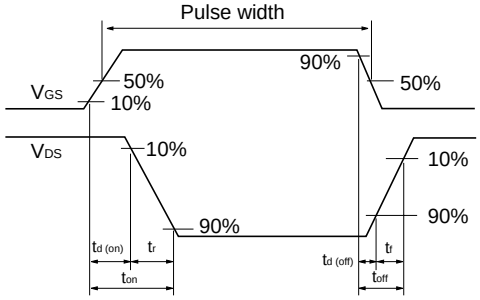


Fig.14 Switching time waveforms

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